

SANYO

N-Channel MOS FET

HIGH-SPEED POWER SWITCHING APPLICATIONS

Features

Low-on resistance, very high-speed switching, converters

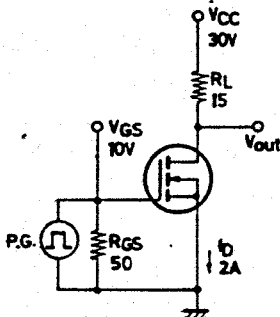
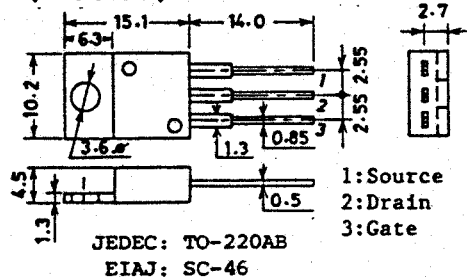
Absolute Maximum Ratings at Ta=25°C

| | | | unit |
|-----------------------------|---------------------|-------------|------|
| Drain to Source Voltage | V _{DS} | 60 | V |
| Gate to Source Voltage | V _{GS} | ±20 | V |
| Drain Current(DC) | I _D | 5 | A |
| Peak Drain Current(Pulse) | I _{D peak} | 10 | A |
| Allowable Power Dissipation | P _D | 40 | W |
| Junction Temperature | T _J | 150 | °C |
| Storage Temperature | T _{stg} | -55 to +150 | °C |

Electrical Characteristics at Ta=25°C

| | | | min | typ | max | unit |
|------------------------------|----------------------|--|-----|-----|------|------|
| D-S Breakdown Voltage | V _{DSS} | I _D =1mA, V _{GS} =0 | 60 | | | V |
| Drain Current | I _{DSS} | V _{DS} =60V, V _{GS} =0 | | | 100 | uA |
| G-S Leakage Current | I _{GSS} | V _{GS} =±20V, V _{DS} =0 | | | ±100 | nA |
| Cutoff Voltage | V _{GS(off)} | V _{DS} =10V, I _D =1mA | 1.5 | | 4.0 | V |
| Forward Transfer Admittance | y _{fs} | V _{DS} =10V, I _D =2.5A | 1.4 | 2.0 | | S |
| Saturation Resistance | r _{DS(on)} | I _D =2.5A, V _{GS} =10V | | 0.2 | 0.3 | ohm |
| Input Capacitance | c _{iss} | V _{DS} =20V, f=1MHz | | 350 | | pF |
| Output Capacitance | c _{oss} | V _{DS} =20V, f=1MHz | | 230 | | pF |
| Reverse Transfer Capacitance | c _{rss} | V _{DS} =20V, f=1MHz | | 85 | | pF |
| Turn-on Time | t _{on} | I _D =2A, V _{GS} =10V | | 35 | | ns |
| Turn-off Time | t _{off} | I _D =2A, V _{GS} =10V | | 55 | | ns |

Note: Be careful in handling the 2SK686 because it has no protect diode between gate and source.

Switching Time Test Circuit**Case Outline 2052A (unit:mm)**

These specifications are subject to change without notice.